







## Electronic Modules for Industrial Applications u...

and its Applications, Experiment . using Data Acquisition device and simulation of MEMS sensors

Interaction Session

8) For mixed ambient growth kinetics of wet oxidation process, which of the following is correct?	1 point
<ul> <li>Substrate doping can affect growth kinetics at lower temperature</li> <li>Rate depends on partial pressure of particular oxidant</li> <li>It depends on substrate orientation</li> <li>All of these</li> </ul>	3
No, the answer is incorrect. Score: 0	
Accepted Answers: All of these	Ŗ
<ul> <li>9) Mask aligner is used to:</li> <li>I. Alignment of wafer to mask</li> <li>II. Coat photoresist on wafer</li> <li>III. Expose the coated wafer</li> <li>IV. Developing the pattern, printed on wafer</li> </ul>	1 point
<ul> <li>1, 11</li> <li>11, 111</li> <li>1, 111</li> <li>11, 117</li> </ul>	
No, the answer is incorrect. Score: 0	
Accepted Answers: /, ///	
10Determine the roll-off for the filter circuit shown below	1 point
<ul> <li>40 dB/decade</li> <li>60 dB/decade</li> <li>20 dB/decade</li> <li>80 dB/decade</li> <li>No, the answer is incorrect.</li> <li>Score: 0</li> <li>Accepted Answers:</li> <li>20 dB/decade</li> </ul>	
11)Consider the circuit shown in the figure below. If input V1 =3 Vp-p sine wave, compute the output voltage of the op-amp U2	1 point
<ul> <li>3 Vp-p Sine wave</li> <li>1.5 Vp-p sine wave</li> <li>3 V DC</li> <li>1.5 V DC</li> </ul> No, the answer is incorrect.	
Score: 0 Accepted Answers:	

1.5 V DC

12For the circuit shown in the question 10, select the correct operation *o points* of the circuit

<ul> <li>Simple low pass filter</li> <li>Half-wave rectifier with filter</li> <li>Full-wave rectifier with filter</li> <li>Peak detector</li> </ul>				
No, the answer is incorrect. Score: 0				
Peak detector				
13Jn ion-assisted etching process, CHF3 is used in: 1 point				
Dry etching of silicon dioxide				
Dry etching of silicon nitride				
Wet etching of silicon dioxide				
Dry etching of silicon dioxide and silicon nitride				
No, the answer is incorrect. Score: 0				
Accepted Answers:				
Dry etching of silicon dioxide and silicon nitride				
14/Which of the below statements are correct:       1 point         i.       Dry oxidation is about 5 times faster than wet oxidation         ii.       Dry oxidation is mainly used for creating thin oxide layers and wet oxidation for thicker ones         iii.       Dry oxidation is used for making field oxide layers and wet oxidation for gate oxides         iv.       Dry oxidation gives better quality oxide layers as compared to wet oxidation				
i, ii, iii, and iv				
ii and iv				
ii, iii and iv				
i, ii, and iv				
No, the answer is incorrect. Score: 0				
Accepted Answers: ii and iv				
15Which of the following is false? 1 point				
Contact mode lithography gives better resolution than other two modes				
In contact mode lithography the mask may get contaminated by photoresist.				
Effect of diffraction of light is minimum for contact mode lithography.				
$igodoldsymbol{\square}$ Contact mode lithography is not efficient for batch production.				
No, the answer is incorrect. Score: 0				
Accepted Answers: Contact mode lithography gives better resolution than other two modes				
16Consider the circuit shown in figure below, compute the output1 pointvoltage of U2 op-amp at t = $0.5s$ Note: Consider the op-amp is supplied with $\pm 15$ V				

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<ul> <li>10 V</li> <li>20 V</li> <li>15 V</li> </ul>	
No, the answer is incorrect. Score: 0 Accepted Answers: 10 V	ي ي ي
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